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(54) **DISPLAY SYSTEM WITH SINGLE CRYSTAL
SI THIN FILM TRANSISTORS**

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16, 2006.

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G02F 1/1343 (2006.01)
G02F 1/1339 (2006.01)

(52) **U.S. Cl.** **349/139; 349/155**

(58) **Field of Classification Search** **349/139,**
349/155

See application file for complete search history.

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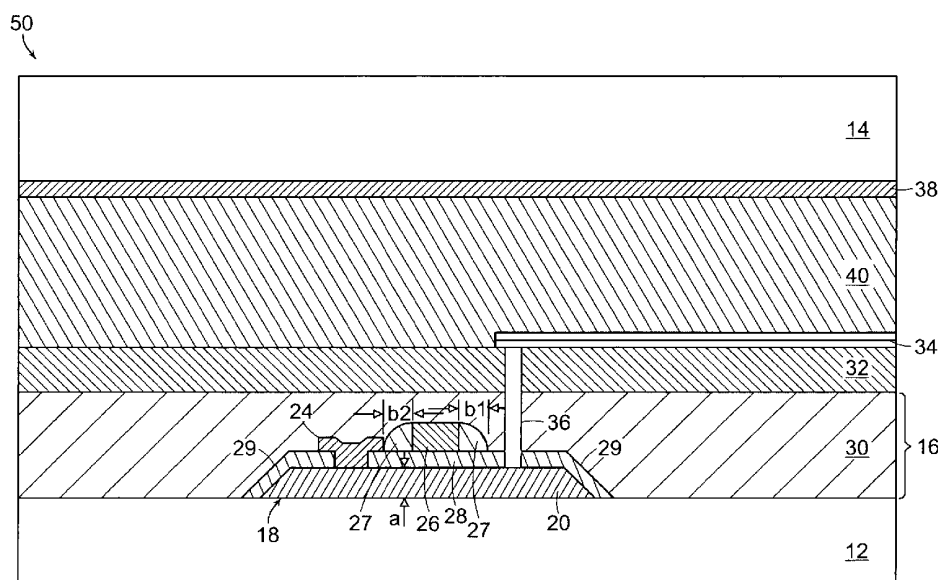
Primary Examiner—K. Cyrus Kianni

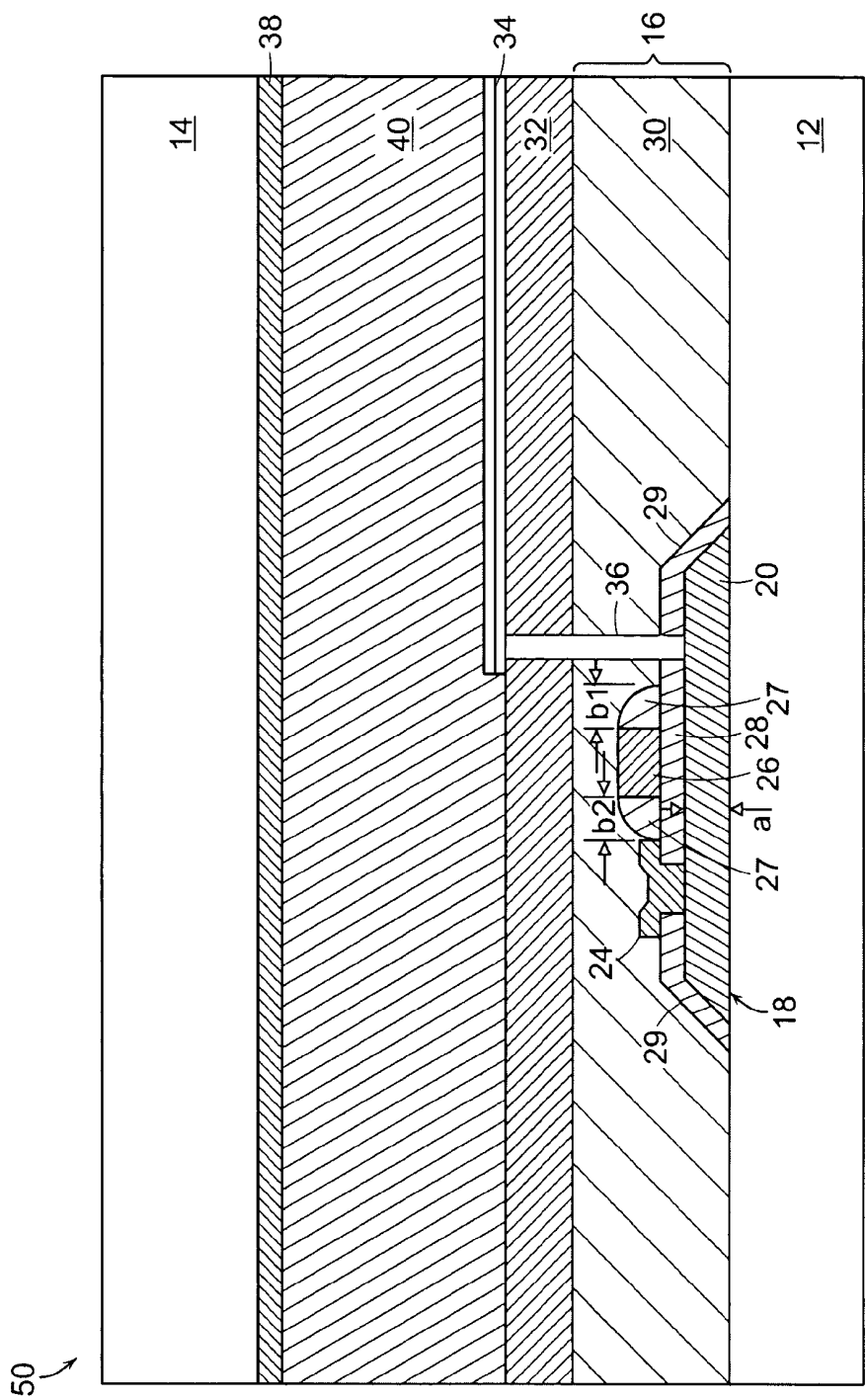
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(57) **ABSTRACT**

A liquid crystal display comprises a display panel that
includes at least one pixel transistor, at least one pixel elec-
trode in electrical communication with the pixel transistor, at
least one common electrode, and a liquid crystal material
between the pixel electrode and the common electrode. The
pixel transistor includes a thin film layer of essentially single
crystal silicon that has a thickness in a range of between about
100 nm and about 200 nm. The pixel electrode has a thickness
in a range of between about 5 nm and about 20 nm. The
common electrode has a thickness of between about 50 nm
and about 200 nm.

25 Claims, 6 Drawing Sheets





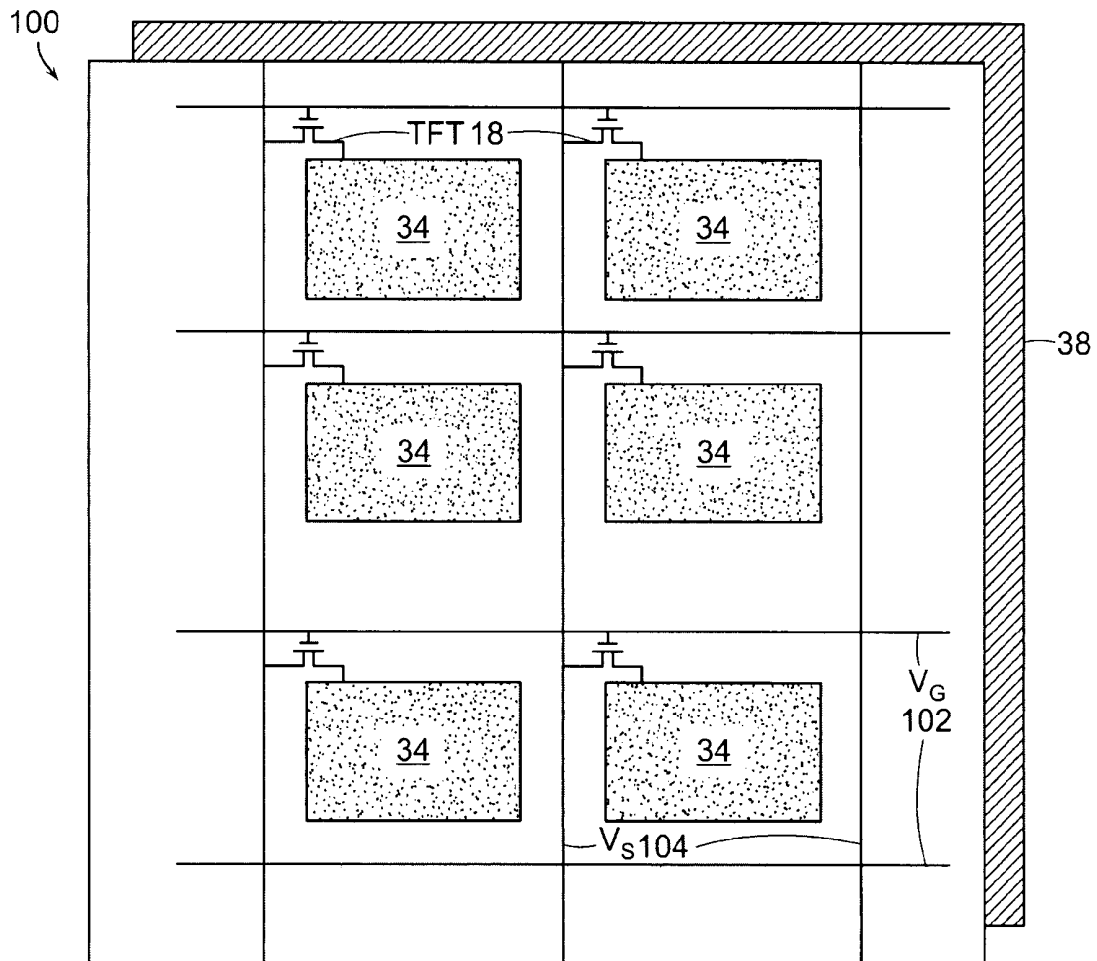


FIG. 3

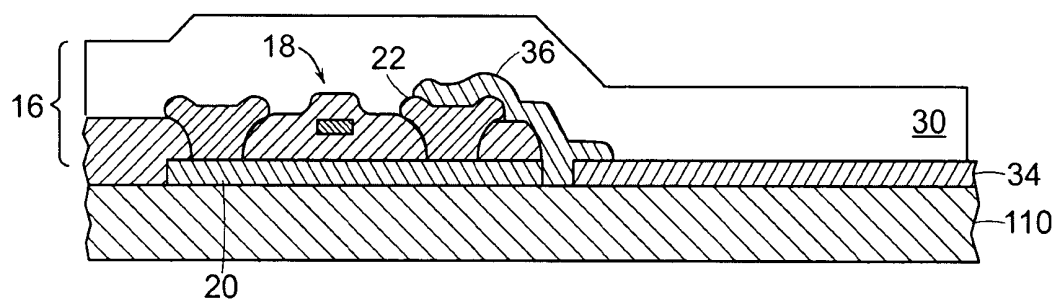


FIG. 4A

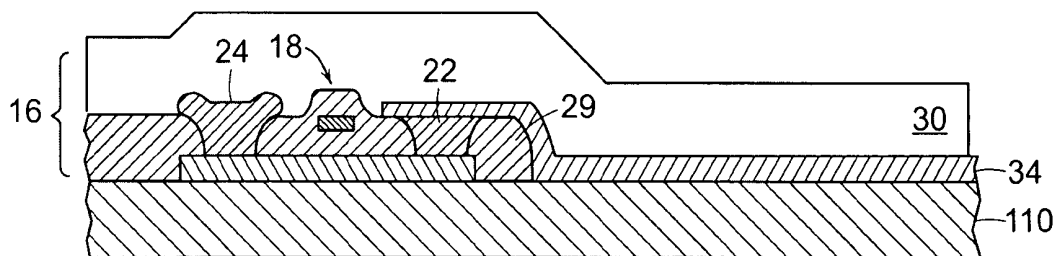


FIG. 4B

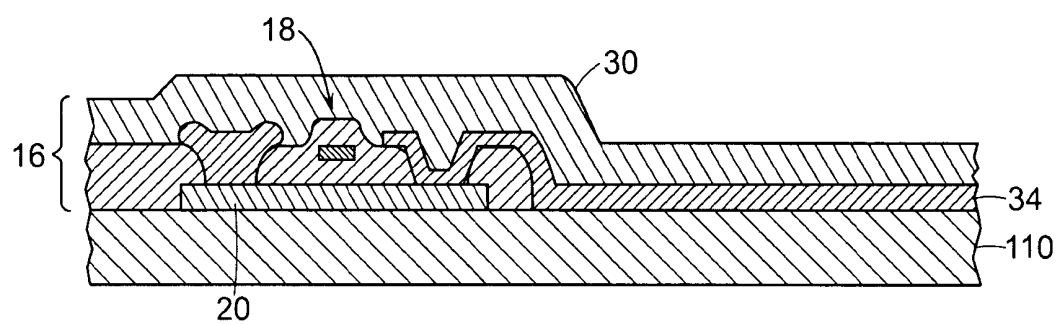


FIG. 4C

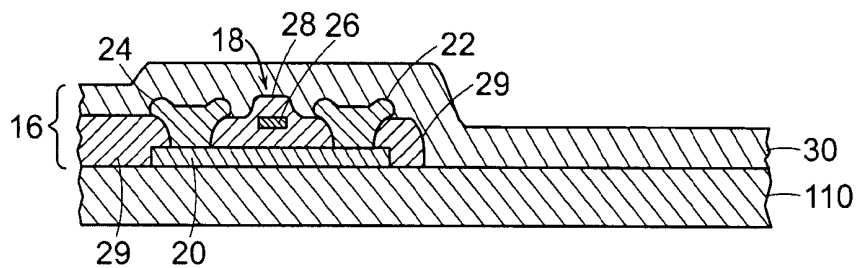


FIG. 5A

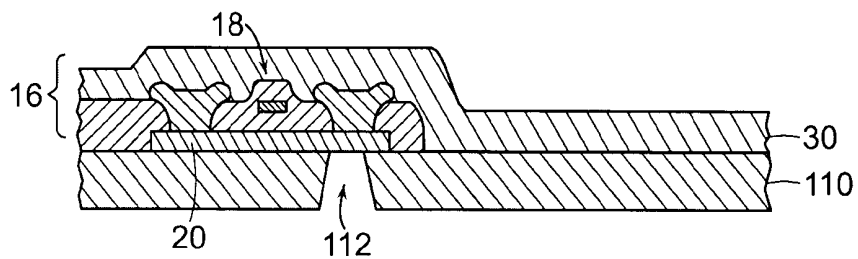


FIG. 5B

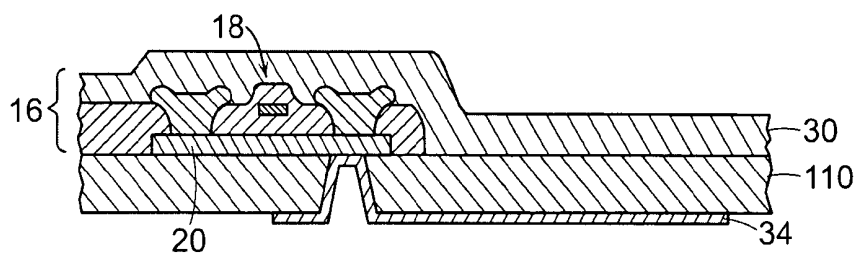


FIG. 5C

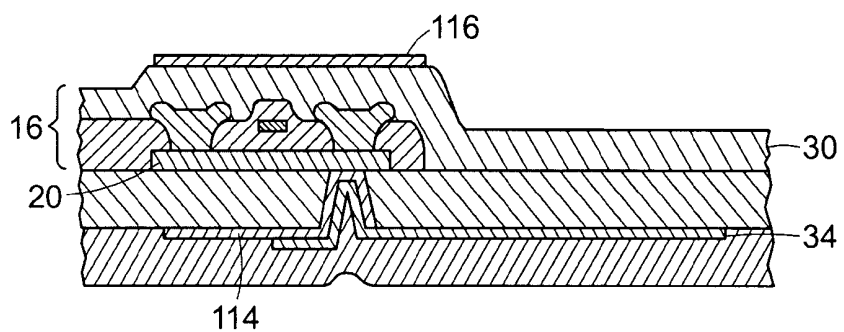


FIG. 5D

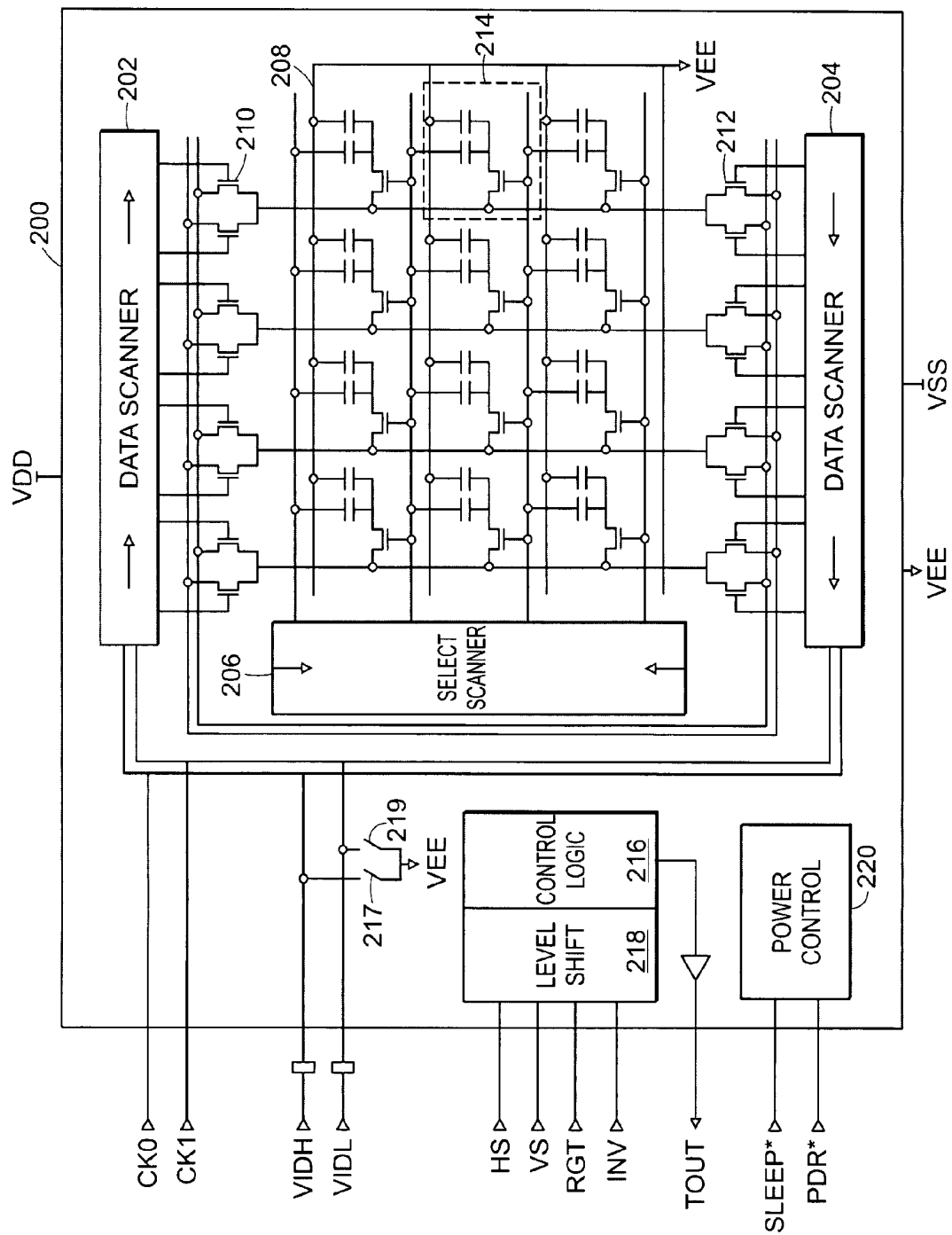


FIG. 6

DISPLAY SYSTEM WITH SINGLE CRYSTAL SI THIN FILM TRANSISTORS

RELATED APPLICATION

This application claims the benefit of U.S. Provisional Application No. 60/838,014, filed on Aug. 16, 2006, the entire teachings of which are incorporated herein by reference.

BACKGROUND

Active matrix color liquid crystal displays (LCDs) generally include five different components: a white light source, a first polarizing film that is mounted on one side of a display panel including an array of pixels defined by arrays of pixel electrodes and thin-film pixel transistors (TFTs), a color filter plate containing at least three primary colors arranged into pixels covered with a transparent common electrode and finally a second polarizing film. A liquid crystal material is disposed between the pixel and common electrodes. This material will rotate the polarization of light when an electric field is applied across it. Thus, when a particular pixel of the display is turned on, the liquid crystal material rotates polarized light transmitted through the material so that it will pass through the second polarizing filter.

For pixel TFTs, various types of silicon have been used, including amorphous silicon, polycrystalline silicon, and single crystalline silicon. Amorphous silicon TFTs generally have poor transistor performance because of very low electron mobility of amorphous silicon. As a result, the amorphous silicon TFTs can only deliver low current density, limiting their use to large-size LCD panels that can accommodate large-size TFTs. Polycrystalline silicon TFTs can in part address the problem associated with amorphous silicon TFTs because the electron mobility of polycrystalline silicon is much higher, but these materials still have a lower electron mobility than single crystalline silicon as they have crystalline defects (such as grain boundary) which can impact TFT performance. Single crystal TFTs have the highest performance, and they can be used for displays with very high pixel density, for example, higher than 100 pixels per inch. In addition, single crystal TFTs have high frequency response, allowing the control electronic circuits to be monolithically integrated within the display panel.

Generally, conventional single crystal TFTs employed in LCDs in the art have a relatively thick silicon layer, for example, having a thickness of about 300 nm or greater. With such thickness, the pixel TFTs may have relatively high photosensitivity (e.g., backlighting and/or ambient light photosensitivity), which can result in current leakage of pixel TFTs. Such current leakage of pixel TFTs, in turn, can cause a relatively low display contrast ratio and/or high image retention.

Thus, a need exists for a method of forming a high quality TFT at each pixel of an LCD that can address problems associated with conventional TFTs, especially forming TFTs that can operate at high speeds, that have reduced photosensitivity, and that can be fabricated easily and at low cost.

SUMMARY OF THE INVENTION

The present invention generally relates to liquid crystal displays (LCDs) employing at least one thin-film pixel transistor having a thin film layer of essentially single crystal silicon (Si) that has a thickness in a range of between about

100 nm and about 200 nm, and to methods of fabricating such LCDs using thin films of essentially single crystal silicon.

In one embodiment, the present invention is directed to a liquid crystal display. The liquid crystal display comprises a display panel that includes at least one pixel transistor, at least one pixel electrode in electrical communication with the pixel transistor, at least one common electrode, and a liquid crystal material between the pixel electrode and the common electrode. The pixel transistor includes a thin film layer of essentially single crystal Si that has a thickness in a range of between about 100 nm and about 200 nm. The pixel electrode has a thickness in a range of between about 5 nm and about 20 nm. The common electrode has a thickness of between about 50 nm and about 200 nm.

In another embodiment, the present invention is directed to a method of preparing a liquid crystal display as described above. The method includes forming at least one pixel transistor that includes a thin film layer of essentially single crystal Si that has a thickness in a range of between about 100 nm and about 200 nm. At least one pixel electrode having a thickness in a range of between about 5 nm and about 20 nm is formed, wherein the pixel electrode is in electrical communication with the pixel transistor. At least one common electrode having a thickness in a range of between about 50 nm and about 200 nm is formed. A liquid crystal layer including a liquid crystal material is formed between the pixel electrode and the common electrode.

An LCD of the invention, employing an array of pixel TFTs, each of which includes a thin film layer of essentially single crystal Si that has a thickness in a range of between about 100 nm and about 200 nm, can provide a high display contrast ratio. In particular, this thickness of the Si thin film layer is relatively very thin compared with a typical thickness of about 300 nm or greater of conventional transistors employed in LCDs in the art. With such relatively thin TFTs, photosensitivity of single crystal Si of the TFTs (backlighting and/or ambient light photosensitivity) can be substantially reduced, which results in reduction of current leakage of the TFTs. This reduction of current leakage of the TFTs can provide a relatively high display contrast ratio, even when LCDs, in which they are incorporated, are being used in ambient (or external) light environment, or when backlighting is very bright.

Also, an LCD of the present invention, employing TFTs of essentially single crystal Si, can provide better performance, such as higher pixel density and faster frequency response, than LCDs employing amorphous Si TFTs or polycrystalline TFTs.

The LCDs of the invention can be used for a variety of applications, including night visions, cell phones, personal computers, electronic viewfinders, for example, for camcorders and digital cameras, portable video eyewear to watch movies, music videos and sporting events on-the-go, and for playing games, etc.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic drawing showing a cross-sectional view of one embodiment of a liquid crystal display device of the invention.

FIG. 2 is a schematic drawing showing a cross-sectional view of another embodiment of a liquid crystal display device of the invention.

FIG. 3 is a schematic drawing illustrating an active matrix pixel structure of one embodiment of a liquid crystal display device of the invention.

FIGS. 4A-4C are schematic drawings illustrating some embodiments of a method of fabricating a liquid crystal display device of the invention.

FIGS. 5A-5D are schematic drawings illustrating other embodiments of a method of fabricating a liquid crystal display device of the invention.

FIG. 6 is a schematic circuit diagram of an integrated control circuit that can be employed in the invention.

DETAILED DESCRIPTION OF THE INVENTION

The foregoing will be apparent from the following more particular description of example embodiments of the invention, as illustrated in the accompanying drawings in which like reference characters refer to the same parts throughout the different views. The drawings are not necessarily to scale, emphasis instead being placed upon illustrating embodiments of the present invention.

The present invention relates to LCDs employing at least one pixel transistor having a thin film layer of essentially single crystal Si that has a thickness in a range of between about 100 nm and about 200 nm, and to methods of fabricating such LCDs. As used herein, the term "essentially single crystal Si film" means a film of crystalline Si in which a majority of the crystalline Si shows a common crystalline orientation and extends over an area in a plane of the film for at least 0.01 cm². The term also includes a film of completely single crystal Si. Such films can be formed using any suitable technique known in the art.

In some embodiments, the pixel transistor is a metal-oxide thin film transistor that includes a drain, a source, a gate oxide layer over the silicon thin film layer, and a gate terminal over the gate oxide layer, wherein each of the drain and source independently are in electrical contact with the silicon thin film layer.

FIG. 1 is a schematic cross-sectional view of one embodiment of the LCDs of the invention. Referring to FIG. 1, the LCD of FIG. 1 comprises display panel 10 that includes first transparent substrate 12 and second transparent substrate 14. TFT structure 16 that includes at least one thin-film pixel transistor ("pixel TFT") 18 and passivation layer 30. Insulating layer 32 separates TFT structure 16 from pixel electrode 34. Interconnect 36 provides electrical interconnection between pixel TFT 18 and pixel electrode 34. Pixel electrode 34 and common electrode 38 are partitioned by liquid crystal layer 40. Optional bonding layer 42 is located between first transparent substrate 12 and passivation layer 30.

Any suitable transparent substrate known in the art can be used for first and second transparent substrates 12 and 14. Suitable examples include glass, fused silica, sapphire, quartz, and transparent plastics. Preferably, glass, fused silica or sapphire is employed as first and second transparent substrates 12 and 14.

TFT structure 16, positioned between first and second transparent substrates 12 and 14, includes at least one pixel TFT 18, and passivation layer 30 disposed over a first major side of pixel TFT 18. Pixel TFT 18 includes thin film layer 20 of essentially single crystal Si ("Si thin film layer 20"), metal contacts 22 and 24, gate terminal 26, spacer 27, and gate oxide layer 28 that partitions Si thin film layer 20 and gate terminal 26 from each other. One of metal contacts 22 and 24 forms a drain of pixel TFT 18, while the other of the metal contacts forms a source of pixel TFT 18. Metal contacts 22 and 24 each independently are positioned on Si thin film layer 20 and in electrical communication with Si thin film layer 20. Insulating layer 29 is positioned at periphery of Si thin film layer 20, as shown in FIG. 1.

Si thin film layer 20 has a thickness ("a" shown in FIG. 1) in a range of between about 100 nm and about 200 nm. In one embodiment, the thickness is in a range of between about 150 nm and about 200 nm, such as about 200 nm.

Spacer 27 is positioned between at least one of gate terminal 26 and metal contact 22, and gate terminal 26 and metal contact 24, as shown in FIG. 1. In one embodiment, spacer 27 has a width ("b1" in FIG. 1), measured from a gate terminal-spacer boundary, in a range of between about 300 nm and about 800 nm. In another embodiment, spacer 27 has a width ("b2" in FIG. 1), measured from a gate terminal-spacer boundary, in a range of between about 300 nm and about 800 nm. In yet another embodiment, each of widths "b1" and "b2" independently is in a range of between about 500 nm and about 800 nm, such as about 600 nm.

Gate oxide layer 28 has a thickness in a range of between about 50 nm and about 150 nm, such as in a range of between about 50 nm and about 100 nm (e.g., about 70 nm or about 75 nm). Any suitable gate oxide material known in the art can be used in the invention for gate oxide layer 28. Suitable examples include silicon dioxide, silicon nitride and silicon oxynitride. In a certain embodiment, gate oxide layer 28 includes silicon dioxide.

Metal contacts 22 and 24 can be made of any suitable electrically conductive metal material, such as aluminum, copper or tungsten. Generally, gate terminal 26 controls electrical current flow between the metal contacts, i.e., source and drain. Examples of suitable gate materials include polysilicon, tantalum, tungsten, tantalum nitride and titanium nitride. Preferably, polysilicon is employed for gate terminal 26 in the invention. More preferably, the polysilicon gate terminal is doped with an n-type or a p-type dopant to lower its resistivity.

In a certain embodiment, pixel TFT 18 has gate terminal 26 that has a length in a range of between about 0.3 microns and about 1 micron, such as about 0.6 microns, and that has a width in a range of between about 1 micron and about 6 microns, such as about 4 microns. In another certain embodiment, pixel TFT 18 has a total thickness in a range of between about 250 nm and about 500 nm, such as between about 300 nm and 400 nm.

Insulating layer 32 is disposed over a second major side of pixel TFT 18, opposite to passivation layer 30. At least one pixel electrode 34 is positioned over insulating layer 32. Pixel electrode 34, and Si thin film layer 20 of pixel TFT 18 are partitioned from each other by insulating layer 32.

Interconnect 36 of suitable conductive metal, such as aluminum, titanium, titanium-tungsten, tungsten or copper, electrically connects pixel electrode 34 and Si thin film layer 20. Pixel electrode 34 can be formed from polysilicon or a transparent conductive material, such as indium tin oxide, or other metal oxides such as titanium dioxide or zinc oxide. Conductive nitrides, such as aluminum nitride, for example, can also be used. Preferably, pixel electrode 34 includes polysilicon, or alternatively indium tin oxide. Generally, pixel electrode 34 has a thickness in a range of between about 5 nm and about 20 nm.

Common electrode 38 can be formed from a transparent conductive material, such as indium tin oxide, or of other metal oxides, such as titanium dioxide or zinc oxide. Conductive nitrides, such as aluminum nitride, for example, can also be used. In a certain embodiment, common electrode 38 includes an indium tin oxide. Generally, common electrode 38 has a thickness in a range of between about 10 nm and about 20 nm.

Liquid crystal (LC) layer 40 includes a suitable LC material such as a twisted-nematic LC material or vertically aligned LC material. In nematic LCs, the LC

no positional order when there is no external magnetic or electric field, but can be easily aligned by an external magnetic or electric field applied to them. Any suitable twisted nematic LC material known in the art can be used in the invention. Various types of such LC materials are commercially available, for example, from Merck KGa in Germany, such as MLC-6424, MLC-9000-000, MLC-9000-100, MLC-9300-000, MLC-9300-100, TL-203 and also, from Chisso, in Japan, LC materials, such as ZOC-5057-LA, and ZOC-5058-LA. LC material **40** is typically positioned between pixel electrode **34** and common electrode **38**.

For bonding layer **42**, preferably, transparent adhesives, such as transparent epoxy, are employed. Examples of suitable transparent adhesives can be found in the art, for example, in U.S. Pat. No. 5,256,562, the entire teachings of which are incorporated herein by reference.

FIG. 2 shows a schematic cross-sectional view of another embodiment of an LCD of the invention. Referring to FIG. 2, display panel **50** includes first and second transparent substrates **12** and **14**, and TFT structure **16** between first and second transparent substrates **12** and **14**. TFT structure **16** includes at least one pixel TFT **18** and passivation layer **30** that is positioned over a first major surface of pixel TFT **18**, opposite to first transparent substrate **12**. Insulating layer **32** is positioned over passivation layer **30**. Pixel electrode **34** is positioned over insulating layer **32**. Pixel electrode **34** and pixel TFT **18** are in electrical communication with each other via interconnect (or via) **36**. Common electrode **38** is positioned at second transparent substrate **14**. LC layer **40** is positioned between common electrode **38** and pixel electrode **34**. In display panel **50**, pixel TFT **18**, positioned at transparent substrate **12**, includes Si thin film layer **20**, source **24**, gate terminal **26**, and gate oxide layer **28** that partitions Si thin film layer **20** and gate terminal **26** from each other. In display panel **50**, Si thin film layer **20** and pixel electrode **34** are in electrical communication with each other through interconnect **36**. In display panel **50**, a region of interconnect (or via) **36** adjacent to Si thin film layer **20** can function as a drain for pixel TFT **18**. Features of the components of display panel **50**, including preferred features, each independently are as described above for the components of display panel **10**.

Any suitable insulating materials can be employed for spacer **27**, passivation layer **30** and insulating layers **29** and **32**. Suitable examples include silicon dioxide and silicon nitride. In certain embodiments, at least one of spacer **27**, passivation layer **30** and insulating layers **29** and **32** includes silicon dioxide. In certain embodiments, each of spacer **27**, passivation layer **30** and insulating layers **29** and **32** independently includes silicon dioxide. When silicon thin film layer **20** is doped by ion implantation, the spacer **27** lowers the doping level in the silicon layer **20** underneath it because ions are implanted through spacer **27** compared to the source or drain region where there is no spacer.

Referring back to the embodiments of FIGS. 1 and 2, and although not shown in these figures, LC layer **40** of each of display panels **10** and **50** independently can further include alignment films. In some embodiments, the alignment films have different rubbing directions, e.g., 90-degrees from each other. Examples of alignment materials for alignment films include polyimide (Pi) materials, such as SE-7511L, SE-1211 and RN-1566, which are available from Japan Nissan Chemical Industrial Ltd. Other suitable vertical alignment materials are also available from JSR Corporation in Japan. The alignment layer can also be fabricated by a suitable method known in the art.

In some specific embodiments, display panels **10** and **50** of the LCDs of the invention each independently further include

color filters of red, blue or green (not shown). Color filters can be positioned at either transparent substrate **12** or **14**. For example, color filters can be placed at first transparent substrate **12**, such as between first transparent substrate **12** and pixel electrode **34**. Alternatively, color filters are placed at second transparent substrate **14**, for example, between common electrode **38** and second transparent substrate **14**. Any suitable color filter materials can be used in the invention, for example, color filter materials available from Japan Dai Nippon Printing and Fuji Film.

The LCDs of the invention can further employ polarizer layers (not shown) at each side of display panel **10** or **50**. Polarizer layers can be disposed in either a crossed (e.g., normally white LCD) or parallel geometry (e.g., normally black LCD). Any suitable polarizer materials known in the art can be used in the invention.

Although in display panels **10** and **50**, only one pixel TFT **18** and one pixel electrode **34** are shown, it is noted that a plurality of pixel TFTs **18** and a plurality of pixel electrodes **34**, forming an active pixel matrix, can be employed in the invention. In a certain embodiment, as shown in FIG. 3, liquid crystal display **100** of the invention employs an active matrix display including an active pixel matrix of an array of pixel TFTs **18**, an array of pixel electrodes **34**, and one common electrode **38**. As shown in FIG. 3, there is no direct contact between pixel electrodes **34**. Rather, each pixel electrode **34** is electrically connected with gate line V_G **102** and source line V_S **104** through pixel TFT **18**.

The active pixel matrix of arrays of pixel TFTs **18** and pixel electrodes **34** can be made by any suitable methods known in the art, for example by the methods disclosed in U.S. Pat. Nos. 5,206,749, 5,705,424 and 6,608,654, the entire teachings of which are incorporated herein by reference. In one embodiment, TFT structure **16** (see, for example, FIG. 1) (e.g., including an array of pixel TFTs **18**) is made by the methods described in U.S. Pat. No. 5,206,749. As described in U.S. Pat. No. 5,206,749, TFTs **18** is formed from an essentially single crystal Si material having a silicon-on-insulator (SOI) structure. The SOI structure can be fabricated using a number of techniques including recrystallization of non-single crystal Si that has been deposited on a silicon dioxide layer formed on a single crystal Si substrate. This Si or other semiconductor substrate can be removed by etching after bonding of TFT structure **16** to a transparent substrate, such as transparent substrate **12** of FIGS. 1 and 2. Other methods for SOI structure fabrication including the bonding of two wafers with an adhesive and lapping of one wafer to form a thin film and transfer of the thin film onto glass, or alternatively by implantation of oxygen into a silicon wafer, can also be used.

TFT structure **16** onto a transparent substrate. In these latter embodiments, an interconnect (or via), such as interconnect **36** shown in FIG. **1**, is optionally formed to electrically connect pixel TFT **18** of TFT structure **16**, and pixel electrode **34**.

Certain specific embodiments of LCD fabrication methods of the invention are illustrated in FIGS. **4A-4C**. In these embodiments, pixel TFT **18** is fabricated with thin film **20** of essentially single crystal Si, pixel electrode **34** is fabricated, and then the fabricated pixel TFT **18** and pixel electrode **34** are transferred onto a transparent substrate (e.g., glass substrate) for further display fabrication. In FIGS. **4A-4C**, pixel TFT **18** is formed in Si thin film layer **20** over silicon dioxide insulating substrate **10**. The area or region of Si thin film layer **20** in which pixel electrode **34** is to be formed is subjected to a silicon etch to expose the underlying oxide layer **110**. Pixel electrode **34** is then formed on or over the exposed area of insulating layer **110**. The pixel electrode material includes polycrystalline silicon. In FIG. **4A**, pixel electrode **34** is connected to pixel TFT **18** via metal interconnect **36**. In FIG. **4B**, a portion of the deposited pixel electrode **34** extends up insulating layer **29** of transistor **18**, and to contact metallization **22** of pixel TFT **18**. In FIG. **4C**, pixel electrode **34** is formed on or over a portion of the surface of Si thin film layer **20**. Passivation layer **30** is then formed over pixel TFT **18**, as shown in FIGS. **4A-4C**. The formed TFT structure and pixel electrode **34** are then transferred to an optically transparent substrate (e.g., glass substrate), such as transparent substrate **12** as shown in FIG. **1**.

Another certain embodiment of an LCD fabrication method of the invention employs formation of pixel electrode **34** after transfer of TFT structure **16** (e.g., including an array of pixel TFTs **18**) onto a transparent substrate. In this embodiment, as shown in FIGS. **5A-5D**, after the transfer, pixel electrode **34** is fabricated at an exposed backside of insulating layer **110** on which Si thin film layer **20** has been formed. In FIGS. **5A-5D**, the transfer substrate is not shown. Area **112** is formed through insulating layer **110**, as shown in FIG. **5B**. Pixel electrode **34** is then deposited and patterned to make an electrical contact to pixel TFT **18** (see FIG. **5C**). As shown in FIG. **5D**, an additional metal layer **114** can be formed between pixel electrode **34** and contact area **112** to improve conductivity. Metal layer **114** can act as interconnect (or via) (for example, interconnect (or via) **36** shown in FIG. **1**), and/or can act as an opaque light shield on a first side of TFT structure **16**. A separate light shield region **116** can also be formed on a second side of TFT structure **16**, e.g., over passivation layer **30** in FIG. **5D**.

The structures of FIGS. **4A**, **4B**, **4C**, **5A**, **5C** and **5D**, including pixel TFT **18** and pixel electrode **34**, are then attached to common electrode **38**, and polarization elements (not shown) and an LC material is then inserted into the cavity formed between pixel electrode **34** and common electrode **38**, to form display panel **10** of FIG. **1** or display panel **50** of FIG. **2**.

In forming pixel TFT **18** (see, for example, FIG. **1**), there generally is loss of Si material in Si thin film layer **20**, in particular when the gate oxide **26** is formed and etching the oxide layer **18** to expose Si thin film layer **20** to make ohmic contact for source **24** and drain **22**. In addition, there generally is a loss of Si material in Si thin film layer **20** in a drain area of pixel TFT **18** where interconnect (or via) **36** is formed, partly due to various oxidation and etching processes. In a certain embodiment, such loss of Si material is reduced by employing relatively thin gate oxide **28**, having a thickness, for example, in a range of between about 50 nm and about 100 nm, and preferably between about 50 nm and about 70 nm (e.g., about 60 nm). In another certain embodiment, a selec-

tive dry etching or wet etching process, having a silicon oxide:Si selectivity ratio of over about 5:1, such as a silicon oxide:Si selectivity ratio in a range between about 10:1 and about 100:1, is employed for etching processes involving Si thin film layer **20**, for example, the etching process for producing contact area **112** of FIG. **5B**. With one or more these methodologies, the residual portion of Si thin film layer **20**, where interconnect (or via) **36** is formed, can have a thickness in a range of between about 100 nm and about 200 nm. With such thickness, a reliable metal contact to Si thin film layer **20** can be achieved.

Si thin film layer **20** of pixel TFT **18** can include a P-type transistor channel or an N-type transistor channel. In a specific embodiment, Si thin film layer **20** includes a P-type transistor channel. In a more specific embodiment, Si thin film layer **20** is implanted with 120,000 eV (electron volt) P⁺ (positive phosphorous ion) to a level of about $2 \times 10^{12} \text{ cm}^{-2}$, and with 80,000 eV BF²⁺ (doubly charged positive boron fluoride ion) to a level of about $2.4 \times 10^{12} \text{ cm}^{-2}$, to thereby form a P-type transistor channel and a main body.

In another specific embodiment, a lightly doped drain (LDD) structure is employed for pixel TFT **18** in the invention to reduce pixel transistor leakage current. The LDD structure can be made between a transistor gate region and a source or drain region. The impurity level (i.e., doping concentration) in the LDD region is moderately high, but lower than the level in the source and drain region. In a more specific embodiment, the LDD structure utilizes spacer **27** (see FIGS. **1** and **2**) around gate terminal **26**. Spacer widths "b1" and "b2" shown in FIGS. **1** and **2**, for example, each independently are in a range of between about 300 nm and about 800 nm, such as between about 500 nm and about 800 nm (e.g., about 600 nm each). The doping level in the silicon layer **20** of the LDD region is lower than in the source and drain region because the ion implantation in the LDD region is performed through the spacer layer **27**.

In yet another specific embodiment, pixel TFT **18** employs an LDD structure that utilizes spacer **27** (see FIGS. **1** and **2**) around gate terminal **26**, and has a threshold voltage of about -1.6

shown in FIG. 6). The integrated control circuits drive the active matrix pixel array **208**. An RGT input selects one of the two data scanners (**202** and **204**) for left-to-right (**202**) or right-to-left (**204**) horizontal scanning. Select scanner **206** scans vertically from top to bottom. Data scanners **202**, **204** accept logic-level clock inputs directly from the input pads, thereby reducing the power dissipation and skew otherwise associated with internal clock drivers (not shown). Complementary video signals are accepted on the AC-coupled VIDH and VIDL inputs, with internal switches **217** and **219**, respectively, restoring DC levels during the horizontal retrace interval. The VIDH and VIDL signals carry video signals to the transmission gates **210** and **212**.

In some embodiments, a CMOS control circuitry is employed in the invention. In a specific embodiment, at least one control TFT that includes Si thin film layer **20** having a thickness in a range of between about 100 nm and about 200 nm is employed in the integrated control circuits for driving the display panel (e.g., display panel **208**) of an LCD of the invention. In one specific embodiment, at least one of data scanners **202** and **204**, internal switches **217** and **219**, clock driver, shift register, and level shifter **218** employs such a control TFT. Features of such control TFT, including preferred features, are as described above for pixel TFT **18**. In another specific embodiment, the CMOS control circuitry is formed in the same Si thin film material in which pixel TFTs **18** are formed. In this embodiment, the CMOS control circuitry is capable of being fully interconnected to a display panel (e.g., display panel **208**) of an LCD of the invention, without the need for wires and wire bonding.

In a certain embodiment, the integrated control circuits (ICCs) include a shift register circuit which directly accepts low voltage clock signal inputs without using clock buffers, as described in U.S. Provisional Application No. 60/860,059, filed Nov. 20, 2006, the entire teachings of which are incorporated herein by reference. The shift register circuit is adapted to operate with a low voltage swing clock signal, and has a state node driven directly by a single transistor state input.

In another certain embodiment, the integrated control circuits (ICCs) include one or more DC-restore switches that are integrated within an LCD of the invention. In these embodiments, the LCD includes a coupling capacitor coupled at one end to a system input video signal, the coupling capacitor providing a display input video signal having a DC level offset. An LCD panel, such as, display panel **10** or **50**, coupled to another end of the coupling capacitor receives a first display input video signal at a video input for driving the display panel. A switch integrated within the LCD device provides DC restore to the coupling capacitor. Suitable examples of DC-restore switches that can be employed in the invention can be found in U.S. Pat. No. 7,138,993, the entire teachings of which are incorporated herein by reference. In a specific embodiment, the LCD of the invention, in addition to a display panel as described above (e.g., display panel **10** or **50**), includes a system input video signal; a first amplifier having a first gain for amplifying the system input video signal to provide a first display input video signal at an output; a first coupling capacitor coupled at one end to the first amplifier output, the first coupling capacitor providing a first DC level offset to the first display input video signal; a first video input which is integrated in the display panel and coupled to

another end of the first coupling capacitor to receive the first display input video signal for driving the display panel; and a first switch which is integrated in the display panel and coupled to the first video input that provides DC restore to the first coupling capacitor. In another specific embodiment, the first integrated switch provides DC restore to the first coupling capacitor when operated during a retrace interval of the system input video signal. In a more specific embodiment, the LCD of the invention further includes a second amplifier having a second gain for amplifying the system input video signal to provide a second display input video signal, the second gain opposite in polarity to the first gain such that the second display input video signal is a complement of the first display input video signal; a second coupling capacitor coupled at one end to the second amplifier output, the second coupling capacitor providing a second DC level offset to the second display input video signal; a second video input which is integrated in the display panel and coupled to another end of the second coupling capacitor to receive the second display input video signal for driving the display panel; and a second switch which is integrated in the display panel and coupled to the second video input that provides DC restore to the second coupling capacitor. In yet another specific embodiment, the first and second integrated switches provide DC restore to the first and second coupling capacitors, respectively, when operated during a retrace interval of the system input video signal.

In yet another embodiment, a heater circuit is fabricated with the integrated control circuits, which employs a common voltage polysilicon line to supply heat to the display panel of the LCDs of the invention. The common voltage line can also be made with metal silicides, such as tungsten silicide, to supply higher current than the poly silicon line. The common voltage line of the heater line is in controlling relation to common electrode **38**, and is electrically connected to two or more of pixel TFTs **18** at a point other than gate terminal **26**, and has two terminals to provide a first node and a second node. The heater circuit controls voltages provided to both the first node and the second node, such that a voltage difference between the first and the second nodes causes current to flow through the common voltage line, and to thereby heat pixels defined by pixel electrodes **34**. Such a heater circuit is described in U.S. application Ser. No. 11/784,215, filed Apr. 5, 2007, the entire teachings of which are incorporated herein by reference.

The LCDs of the invention can be any types of liquid crystal displays, including transmissive displays. Preferably, the LCDs of the invention are used in head-mounted display systems.

It is noted that definitions provided in this application and reference characters referring to certain components shown in FIGS. 1-6 prevail over those provided in references cited and incorporated by reference herein, if there is any conflict.

EXEMPLIFICATION

Example 1

Performance Data of LCDs of the Invention

A standard LCD as a control, and an LCD of the invention, each of which was a QVGA resolution display, were tested for

their performance. The standard LCD included TFTs having the thickness of about 300-320 nm and the LCD of the invention included TFTs having the thickness of between about 150-200 nm. The pixel electrode material is polycrystalline Si. As shown in Table 1, the LCD of the invention had superior properties, for example, in image retention, photosensitivity, brightness and contrast ratio.

TABLE 1

	Standard LCD	LCD of the Invention	Units
Contrast Ratio	90	115	White/Black
Transmission	2.5%	2.5%	White/Backlight
Max Display Brightness	350	700	cd/m ²
Max Backlight Brightness	14,000	28,000	cd/m ²
Max Ambient Light Photosensitivity (diffused)	200	1000	Lux
Flicker (60 Hz)	-40	-60	dB
Image Retention	1%	0.5%	% of full gray scale

EQUIVALENTS

While this invention has been particularly shown and described with references to preferred embodiments thereof, it will be understood by those skilled in the art that various changes in form and details may be made therein without departing from the scope of the invention encompassed by the appended claims.

What is claimed is:

1. A liquid crystal display, comprising a display panel that includes:

- a) at least one pixel transistor that includes a thin film layer of essentially single crystal silicon that has a thickness in a range of between about 100 nm and about 200 nm, a gate oxide layer over the silicon thin film layer, and a gate terminal over the gate oxide layer;
- b) at least one pixel electrode in electrical communication with the pixel transistor and having a thickness in a range of between about 5 nm and about 20 nm;
- c) at least one common electrode over the pixel electrode having a thickness of between about 50 nm and about 200 nm;
- d) a liquid crystal material between the pixel electrode and the common electrode; and
- e) first and second spacers above the gate oxide layer and sandwiching the gate terminal.

2. The liquid crystal display of claim 1, further including a bonding layer between the transparent substrate and the pixel transistor.

3. The liquid crystal display of claim 1, wherein the thickness of the silicon thin film layer is in a range of between about 150 nm and about 200 nm.

4. The liquid crystal display of claim 3, wherein the thickness of the silicon thin film layer is about 200 nm.

5. The liquid crystal display of claim 1, wherein the pixel electrode includes polysilicon.

6. The liquid crystal display of claim 1, wherein the pixel electrode includes an indium tin oxide.

7. The liquid crystal display of claim 1, wherein the common electrode includes an indium tin oxide.

8. The liquid crystal display of claim 1, further including a first transparent substrate and a second transparent substrate,

wherein the pixel transistor, the pixel electrode, the common electrode, and the liquid crystal material are between the first and the second transparent substrates.

9. The liquid crystal display of claim 8, wherein at least one of the first and the second transparent substrates includes at least one member chosen from glass, fused silica and sapphire.

10. The liquid crystal display of claim 1, wherein the pixel transistor is a metal-oxide thin film transistor that includes a drain, a source, wherein each of the drain and the source independently is in electrical contact with the silicon thin film layer.

11. The liquid crystal display of claim 1, wherein the gate oxide layer has a thickness in a range of between about 50 nm and about 150 nm.

12. The liquid crystal display of claim 1, wherein the gate oxide layer has a thickness in a range of between about 50 nm and about 100 nm.

13. The liquid crystal display of claim 1, wherein the gate oxide layer includes silicon dioxide.

14. The liquid crystal display of claim 1, wherein the gate terminal includes polysilicon.

15. The liquid crystal display of claim 1, wherein at least one of the first and second spacers has a width, measured from a gate terminal-spacer boundary, at the gate terminal, to the source, in a range of between about 300 nm and about 800 nm.

16. The liquid crystal display of claim 15, wherein the width is in a range of between about 500 nm and about 800 nm.

17. The liquid crystal display of claim 16, wherein the width is about 600 nm.

18. The liquid crystal display of claim 1, wherein at least one of the first and second spacers, has a width, measured from a gate terminal-spacer boundary, at the gate terminal, to the drain, in a range of between about 300 nm and about 800 nm.

19. The liquid crystal display of claim 18, wherein the width is in a range of between about 500 nm and about 800 nm.

20. The liquid crystal display of claim 19, wherein the width is about 600 nm.

21. The liquid crystal display of claim 1, further including an interconnect connecting the silicon thin film layer and the pixel electrode, wherein the Si thin film layer and the pixel electrode are in electrical communication with each other through the interconnect.

22. The liquid crystal display of claim 1, further including a control circuit for driving the display panel, which includes a shift register, clock driver and input level shifter.

23. The liquid crystal display of claim 22, wherein the control circuit includes at least one control transistor that includes a thin film layer of essentially single crystal silicon, the silicon thin film layer having a thickness in a range of between about 100 nm and about 200 nm.

24. The liquid crystal display of claim 23, wherein the control transistor is included in at least one of the shift register, clock driver

13

- b) a pixel electrode in electrical communication with the pixel transistor and having a thickness in a range of between about 5 nm and about 20 nm;
- c) at least one common electrode over the pixel electrode having a thickness of between about 50 nm and about 200 nm;
- d) a liquid crystal material between the pixel electrode and the common electrode; and

14

- e) an interconnect connecting the thin film layer of essentially single crystal silicon and the pixel electrode, wherein the thin film layer and the pixel electrode are in electrical communication with each other via the interconnect.

* * * * *

专利名称(译)	具有单晶SI薄膜晶体管的显示系统		
公开(公告)号	US7768611	公开(公告)日	2010-08-03
申请号	US11/893594	申请日	2007-08-16
[标]申请(专利权)人(译)	寇平公司		
申请(专利权)人(译)	高平公司		
当前申请(专利权)人(译)	高平公司		
[标]发明人	TSAUR BOR YEU CHOI HONG K LO JASON		
发明人	TSAUR, BOR-YEU CHOI, HONG K. LO, JASON		
IPC分类号	G02F1/1343 G02F1/1339		
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外部链接	Espacenet USPTO		

摘要(译)

液晶显示器包括显示面板，该显示面板包括至少一个像素晶体管，与像素晶体管电连通的至少一个像素电极，至少一个公共电极，以及在像素电极和公共电极之间的液晶材料。像素晶体管包括基本上单晶硅的薄膜层，其厚度在约100nm和约200nm之间的范围内。像素电极的厚度在约5nm和约20nm之间的范围内。公共电极的厚度在约50nm和约200nm之间。

